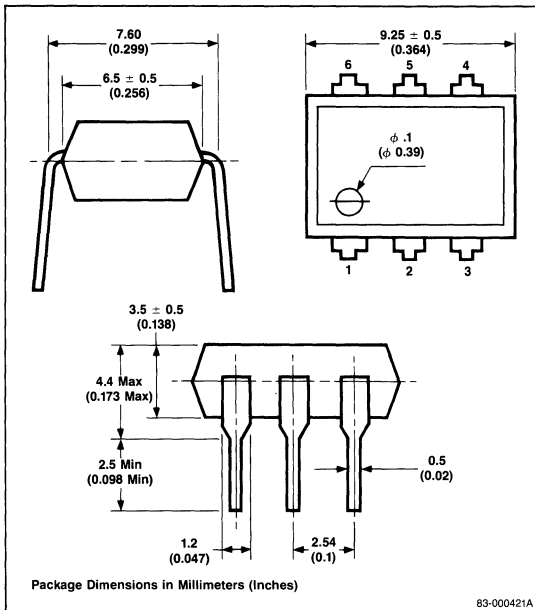


Description

The PS2004B is an optically coupled isolator containing a GaAs light emitting diode and an NPN silicon Darlington photo transistor in a plastic DIP (Dual In-line Package).

Package Dimensions



Features

- High-voltage isolation: 2500V min
- Ultra high transfer ratio: 1300% min
- High output current: 200mA max
- Economical, compact, plastic dual in-line package

Applications

- Copy machine
- Replacement for mechanical and reed relays
- Replacement of pulse transformers

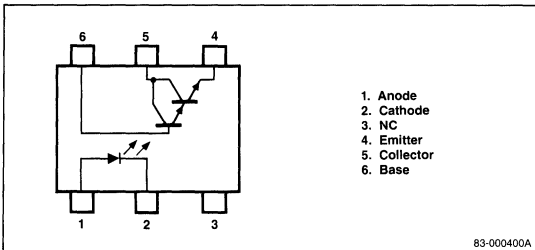
Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Diode	
Reverse Voltage, V_R	5.0V
Forward Current, I_F	50mA
Power Dissipation, P_D	100mW
Transistor	
Collector to Emitter Voltage, V_{CE0}	30V
Collector Current, I_C	200mA
Power Dissipation, P_D	200mW
Total Power Dissipation, P_{TOTAL}	250mW
Isolation Voltage ¹ , BV	2500V _{DC}
Isolation Voltage ¹ , BV	2000V _{AC} (rms)
Storage Temperature, T_{STG}	-55°C to +125°C
Operating Temperature, T_{OPT}	-55°C to +100°C

5

Pin Connection



Electrical Characteristics

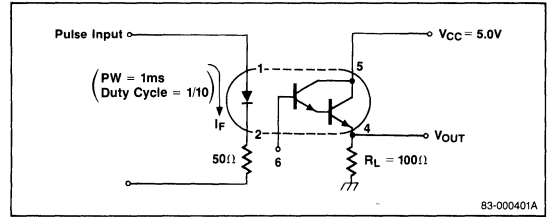
T_A = 25°C

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Diode						
Forward Voltage	V _F		1.4		V	I _F = 20mA
Reverse Current	I _R		5.0		μA	V _R = 4.0V
Junction Capacitance	C	100			pF	V = 0, f = 1.0MHz
Transistor						
Collector to Emitter Dark Current	I _{CEO}		400		nA	V _{CE} = 10V, I _F = 0
Coupled						
Current Transfer Ratio	CTR (I _C /I _F)	1300			%	I _F = 5.0mA, V _{CE} = 2.0V
Collector Saturation Voltage	V _{CE(sat)}		1.2		V	I _F = 5.0mA, I _C = 2.0mA
Isolation Resistance	R ₁₋₂	10 ¹¹			Ω	V _{IN-OUT} = 1.0kV
Isolation Capacitance	C ₁₋₂	0.8			pF	V = 0, f = 1.0MHz
Rise Time	t _r	100			μs	V _{CC} = 5.0V, I _F = 5.0mA, R _L = 100Ω ²
Fall Time	t _f	250			μs	V _{CC} = 5.0V, I _F = 5.0mA, R _L = 100Ω ²

Notes: 1. Measuring Conditions: DC or AC voltage for 1 min at T_A = +25°C, RH = 60% between input (pins 1, 2, and 3 common) and output (pins 4, 5, and 6 common).

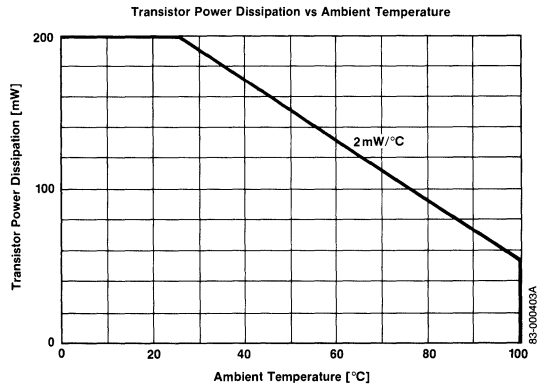
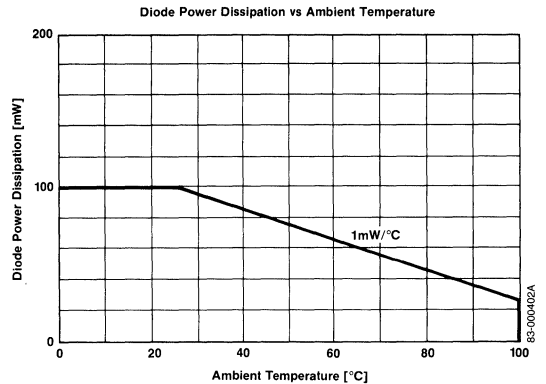
2. Test circuit for switching time.

Test circuit for switching time



Typical Characteristics

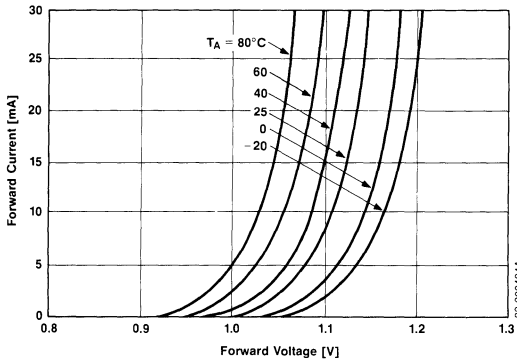
T_A = +25°C



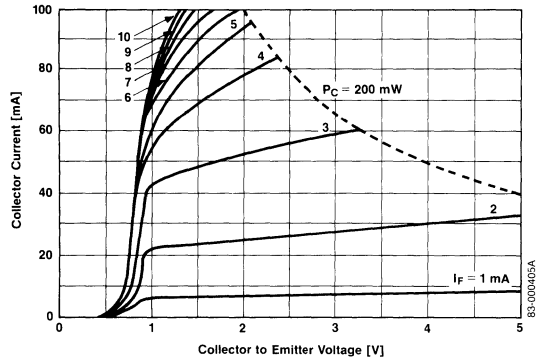
Typical Characteristics (cont)

$T_A = +25^\circ\text{C}$

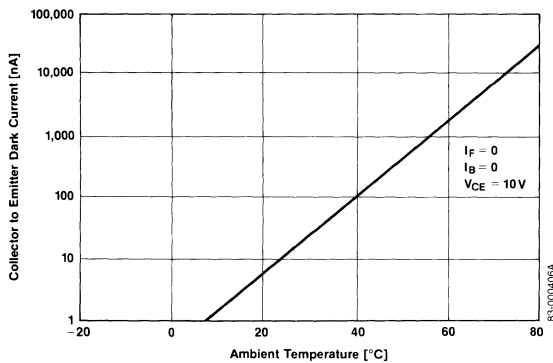
Forward Current vs Forward Voltage



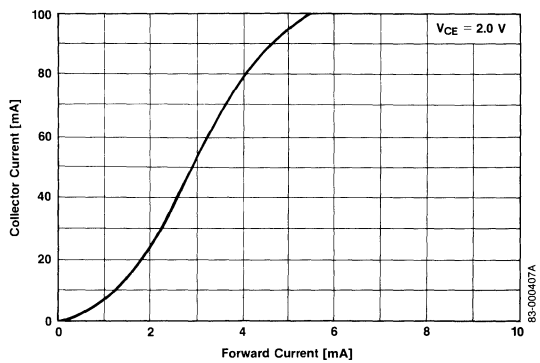
Collector Current vs Collector to Emitter Voltage



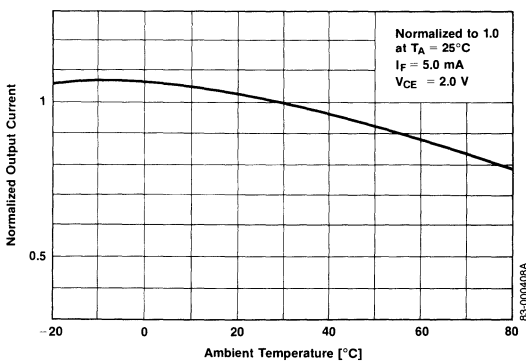
Collector to Emitter Dark Current vs Ambient Temperature



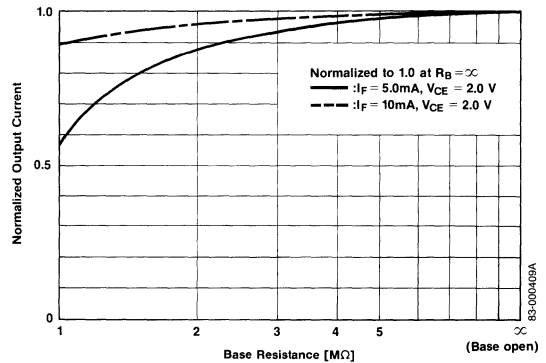
Collector Current vs Forward Current



Normalized Output Current vs Ambient Temperature



Normalized Output Current vs Base Resistance



5